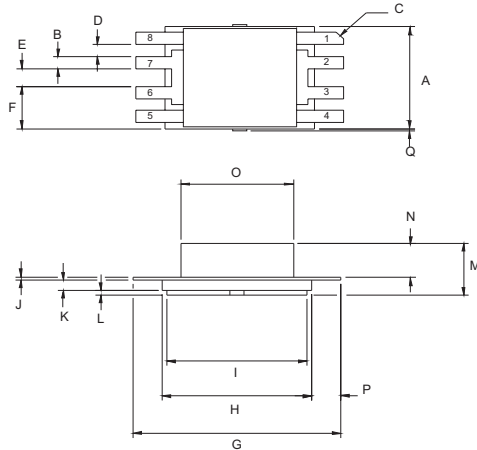


MECHANICAL DATA



DBC1 Package

- PIN 1 Source
- PIN 2 Drain
- PIN 3 Drain
- PIN 4 Source
- PIN 5 Source
- PIN 6 Gate
- PIN 7 Gate
- PIN 8 Source

DIM	mm	Tol.	Inches	Tol.
A	6.47	0.08	.255	.003
B	0.76	0.08	.030	.003
C	45°	5°	45°	5°
D	0.76	0.08	.030	.003
E	1.14	0.08	.045	.003
F	2.67	0.08	.105	.003
G	11.73	0.13	.462	.005
H	8.43	0.08	.332	.003
I	7.92	0.08	.312	.003
J	0.20	0.02	.008	.001
K	0.64	0.02	.025	.001
L	0.30	0.02	.012	.001
M	3.25	0.08	.128	.003
N	2.11	0.08	.083	.003
O	6.35SQ	0.08	.250SQ	.003
P	1.65	0.51	.065	.020
Q	0.13	max	.005	max

**GOLD METALLISED
MULTI-PURPOSE SILICON
DMOS RF FET
6W – 7.2V – 500MHz
SINGLE ENDED**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
from 1 MHz to 1 GHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	58W
BV_{DSS}	Drain – Source Breakdown Voltage	40V
BV_{GSS}	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	20A
T_{stg}	Storage Temperature	-65 to $150^{\circ}C$
T_j	Maximum Operating Junction Temperature	$200^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS} Drain-Source Breakdown Voltage	$V_{GS} = 0$ $I_D = 100mA$	40			V
I_{DSS} Zero Gate Voltage Drain Current	$V_{DS} = 12.5V$ $V_{GS} = 0$			1	mA
I_{GSS} Gate Leakage Current	$V_{GS} = 20V$ $V_{DS} = 0$			1	μA
$V_{GS(th)}$ Gate Threshold Voltage*	$I_D = 10mA$ $V_{DS} = V_{GS}$	0.5		7	V
g_{fs} Forward Transconductance*	$V_{DS} = 10V$ $I_D = 2A$	1.6			S
G_{PS} Common Source Power Gain	$P_O = 6W$	10			dB
η Drain Efficiency	$V_{DS} = 7.2V$ $I_{DQ} = 0.5A$	50			%
VSWR Load Mismatch Tolerance	$f = 500MHz$	20:1			—
C_{iss} Input Capacitance	$V_{DS} = 0$ $V_{GS} = -5V$ $f = 1MHz$			120	pF
C_{oss} Output Capacitance	$V_{DS} = 12.5V$ $V_{GS} = 0$ $f = 1MHz$			80	pF
C_{rss} Reverse Transfer Capacitance	$V_{DS} = 12.5V$ $V_{GS} = 0$ $f = 1MHz$			8	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

THERMAL DATA

$R_{THj-case}$	Thermal Resistance Junction – Case	Max. 3°C / W
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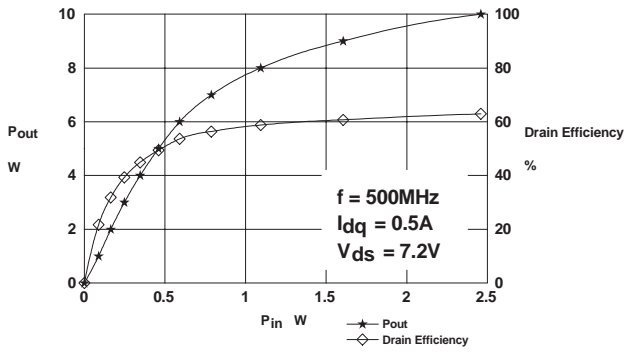


Figure 1 – Power Output and Efficiency vs. Power Input.

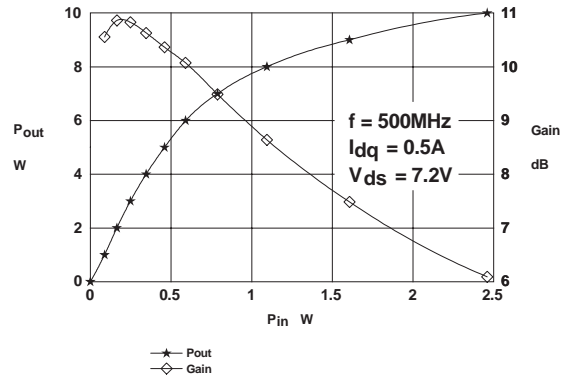


Figure 2 – Power Output & Gain vs. Power Input.

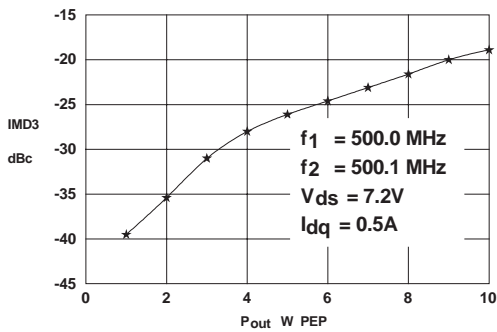


Figure 3 – IMD vs. Output Power.

D1213UK
OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z _S Ω	Z _L Ω
500	2.3 - j0.4	2.1 - j1.9

Typical S Parameters

! $V_{DS} = 7.2V$ $I_{DQ} = 0.2A$
 # MHZ S MA R 50

!Freq MHz	S11		S21		S12		S22	
	mag	ang	mag	ang	mag	ang	mag	ang
70	0.69	-147	6.8	68	0.021	-1	0.77	-160
100	0.74	-153	4.5	59	0.017	10	0.79	-163
150	0.82	-161	2.5	47	0.015	50	0.84	-167
200	0.86	-167	1.6	42	0.024	78	0.87	-169
250	0.89	-172	1.2	35	0.037	83	0.89	-171
300	0.90	-176	1.0	33	0.052	87	0.90	-173
350	0.91	-179	0.7	27	0.064	82	0.91	-175
400	0.92	178	0.6	26	0.082	82	0.92	-177
450	0.93	174	0.5	23	0.095	80	0.93	-178
500	0.93	171	0.5	21	0.116	77	0.93	-179
550	0.93	168	0.4	20	0.130	73	0.94	180
600	0.93	164	0.4	15	0.148	66	0.94	178
650	0.93	162	0.3	18	0.159	66	0.95	177
700	0.92	158	0.3	16	0.173	60	0.94	177
750	0.92	155	0.3	21	0.182	58	0.95	176
800	0.91	153	0.3	23	0.189	56	0.96	175
850	0.92	151	0.3	29	0.207	59	0.96	173
900	0.94	148	0.3	29	0.235	59	0.95	171
950	0.95	144	0.3	31	0.275	56	0.93	170
1000	0.93	140	0.4	29	0.308	52	0.92	168